

IGBT - Power, Co-PAK

N-Channel, Field Stop VII (FS7), Non-SCR, TO247-3L

1200 V, 1.7 V, 100 A

FGY100T120SWD

Description

Using the novel field stop 7th generation IGBT technology and the Gen7 Diode in TO247 3-lead package, FGY100T120SWD offers the optimum performance with low switching and conduction losses for high-efficiency operations in various applications like Solar, UPS, and ESS.

Features

- Maximum Junction Temperature $T_J = 175^\circ\text{C}$
- Positive Temperature Coefficient for Easy Parallel Operation
- High Current Capability
- Smooth and Optimized Switching
- Low Switching Loss
- RoHS Compliant

Applications

- Boost and Inverter in Solar System
- UPS
- Energy Storage System

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

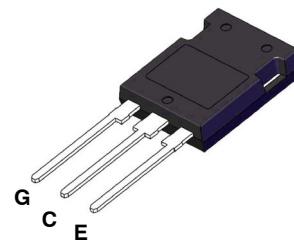
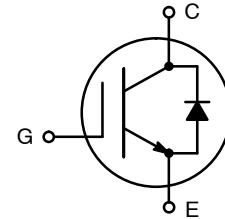
Parameter	Symbol	Value	Unit
Collector-to-Emitter Voltage	V_{CES}	1200	V
Gate-to-Emitter Voltage	V_{GES}	± 20	V
Transient Gate-to-Emitter Voltage		± 30	V
Collector Current	$T_C = 25^\circ\text{C}$ (Note 1)	I_C	A
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	W
	$T_C = 100^\circ\text{C}$		
Pulsed Collector Current	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$ (Note 2)	I_{CM}	A
Diode Forward Current	$T_C = 25^\circ\text{C}$	I_F	A
	$T_C = 100^\circ\text{C}$		
Pulsed Diode Maximum Forward Current	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$ (Note 2)	I_{FM}	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limit by bond wire
2. Repetitive rating: Pulse width limited by max. Junction temperature

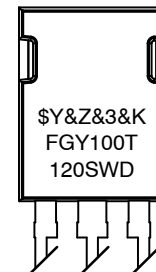
BV_{CES}	$V_{CE(SAT)}$	I_C
1200 V	1.7 V	100 A

PIN CONNECTIONS



TO247-3LD
CASE 340CD

MARKING DIAGRAM



$\$Y$ = onsemi Logo
 $\&Z$ = Assembly Plant Code
 $\&3$ = 3-Digit Date Code
 $\&K$ = 2-Digit Lot Traceability Code
 FGY100T120SWD = Specific Device code

ORDERING INFORMATION

Device	Package	Shipping
FGY100T120SWD	TO-247-3LD (Pb-Free)	30 Units / Tube

FGY100T120SWD

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case for IGBT	$R_{\theta JC}$	0.17	°C/W
Thermal Resistance, Junction-to-Case for Diode		0.29	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS OF IGBT ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}, I_C = 5\text{ mA}$	1200			V
Collector-to-Emitter Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES} / \Delta T_J$			1222		mV/°C
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$			40	μA
Gate-to-Emitter Leakage Current	I_{GES}	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$			±400	nA

ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 100\text{ mA}$	5.6	6.55	7.4	V
Collector-to-Emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 25^\circ\text{C}$	1.35	1.69	2.0	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 175^\circ\text{C}$		2.26		

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{IES}	$V_{GE} = 0\text{ V}, V_{CE} = 30\text{ V}, f = 1\text{ MHz}$		8489		pF
Output Capacitance	C_{OES}			320		
Reverse Transfer Capacitance	C_{RES}			41.4		
Total Gate Charge	Q_G	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 100\text{ A}$		284		nC
Gate-to-Emitter Charge	Q_{GE}			72.4		
Gate-to-Collector Charge	Q_{GC}			101		

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 50\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$		46.4		ns
Turn-Off Delay Time	$t_{d(off)}$			209.6		
Rise Time	t_r			30.4		
Fall Time	t_f			58		
Turn-On Switching Loss	E_{on}			3.1		
Turn-Off Switching Loss	E_{off}	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 100\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$		1.6		mJ
Total Switching Loss	E_{ts}			4.7		
Turn-On Delay Time	$t_{d(on)}$			46.4		ns
Turn-Off Delay Time	$t_{d(off)}$			168		
Rise Time	t_r			72		
Fall Time	t_f			51.2		
Turn-On Switching Loss	E_{on}			8.1		mJ
Turn-Off Switching Loss	E_{off}			2.8		
Total Switching Loss	E_{ts}			10.9		

FGY100T120SWD

ELECTRICAL CHARACTERISTICS OF IGBT ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GE} = 0/15\text{ V}, I_C = 50\text{ A}, V_{CE} = 600\text{ V}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$		38.4		ns
Turn-Off Delay Time	$t_{d(off)}$			244.8		
Rise Time	t_r			28.8		
Fall Time	t_f			92.8		
Turn-On Switching Loss	E_{on}			4.9		mJ
Turn-Off Switching Loss	E_{off}			2.4		
Total Switching Loss	E_{ts}			7.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GE} = 0/15\text{ V}, I_C = 100\text{ A}, V_{CE} = 600\text{ V}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$		41.6		ns
Turn-Off Delay Time	$t_{d(off)}$			196.8		
Rise Time	t_r			64		
Fall Time	t_f			76.8		
Turn-On Switching Loss	E_{on}			11.3		mJ
Turn-Off Switching Loss	E_{off}			3.9		
Total Switching Loss	E_{ts}			15.2		

DIODE CHARACTERISTICS

Forward Voltage	V_F	$I_F = 100\text{ A}, T_J = 25^\circ\text{C}$	1.62	1.82	2.22	V
		$I_F = 100\text{ A}, T_J = 175^\circ\text{C}$		1.87		

DIODE SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 50\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		152		ns
Reverse Recovery Charge	Q_{rr}			2977		nC
Reverse Recovery Energy	E_{rec}			0.9		mJ
Peak Reverse Recovery Current	I_{RRM}			39		A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 100\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		261		ns
Reverse Recovery Charge	Q_{rr}			5636		nC
Reverse Recovery Energy	E_{rec}			1.8		mJ
Peak Reverse Recovery Current	I_{RRM}			43		A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 50\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$		192		ns
Reverse Recovery Charge	Q_{rr}			5275		nC
Reverse Recovery Energy	E_{rec}			1.6		mJ
Peak Reverse Recovery Current	I_{RRM}			55		A
Reverse Recovery Time	t_{rr}	$V_R = 600\text{ V}, I_F = 100\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$		358		ns
Reverse Recovery Charge	Q_{rr}			10858		nC
Reverse Recovery Energy	E_{rec}			3.6		mJ
Peak Reverse Recovery Current	I_{RRM}			61		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

FGY100T120SWD

TYPICAL CHARACTERISTICS

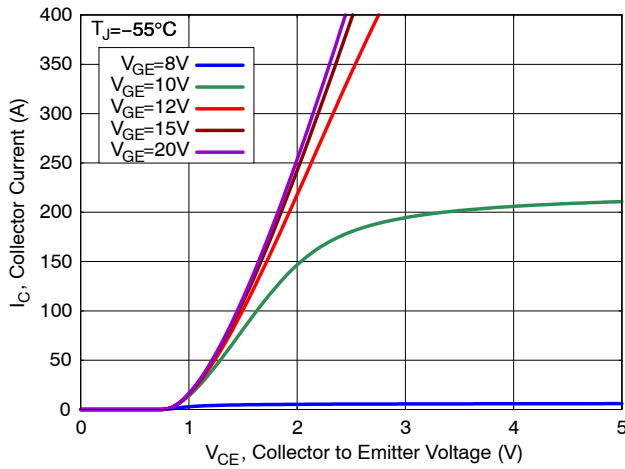


Figure 1. Output Characteristics

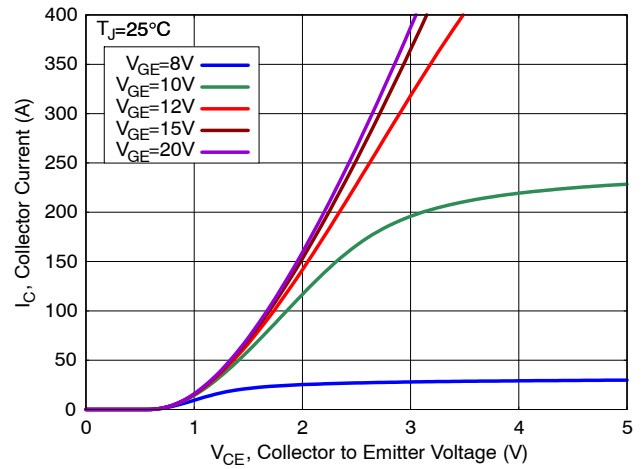


Figure 2. Output Characteristics

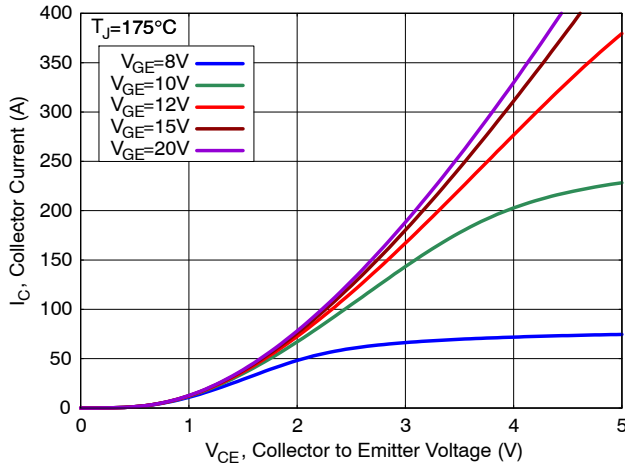


Figure 3. Output Characteristics

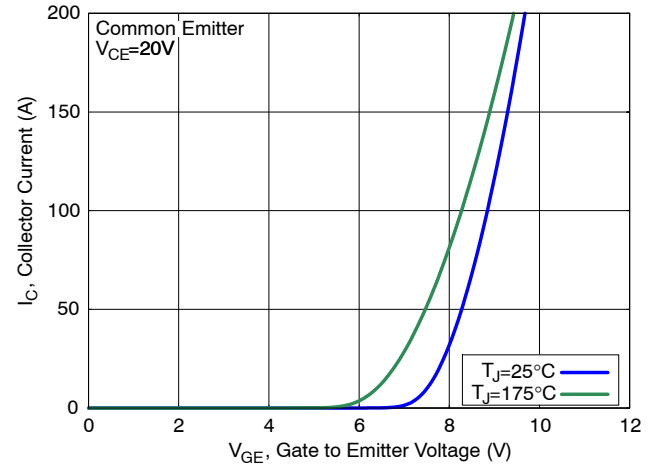


Figure 4. Transfer Characteristics

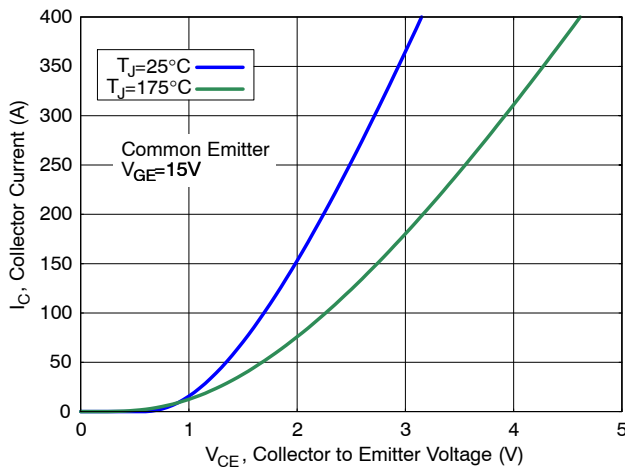


Figure 5. Saturation Characteristics

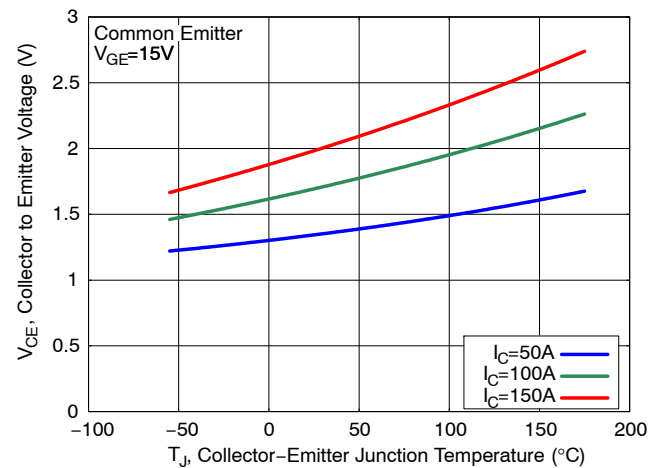


Figure 6. Saturation Voltage vs. Junction Temperature

FGY100T120SWD

TYPICAL CHARACTERISTICS

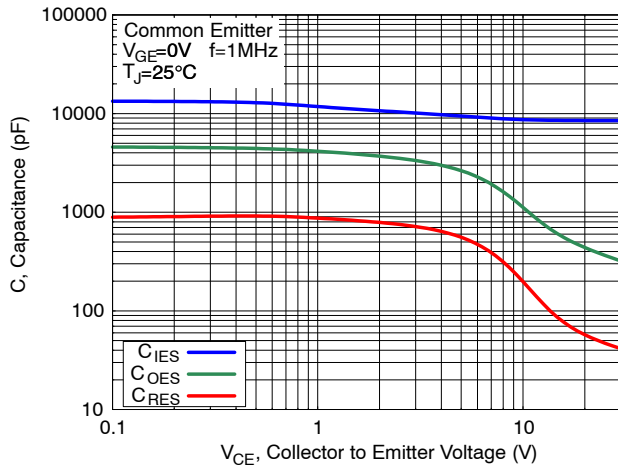


Figure 7. Capacitance Characteristics

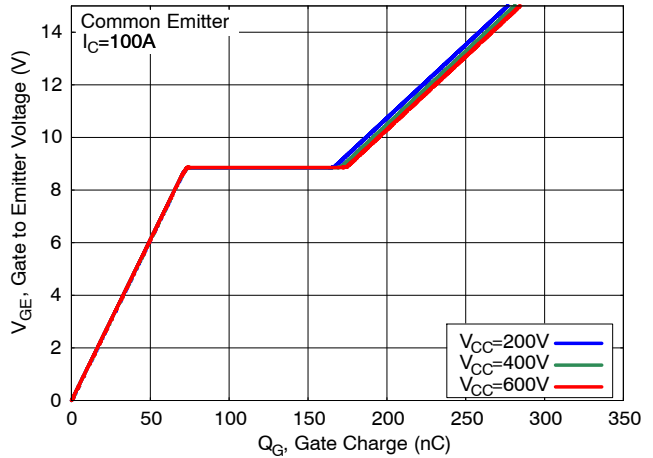


Figure 8. Gate Charge Characteristics

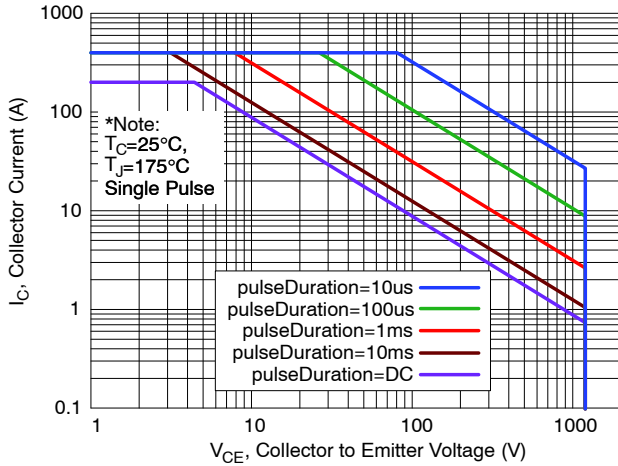


Figure 9. SOA Characteristics

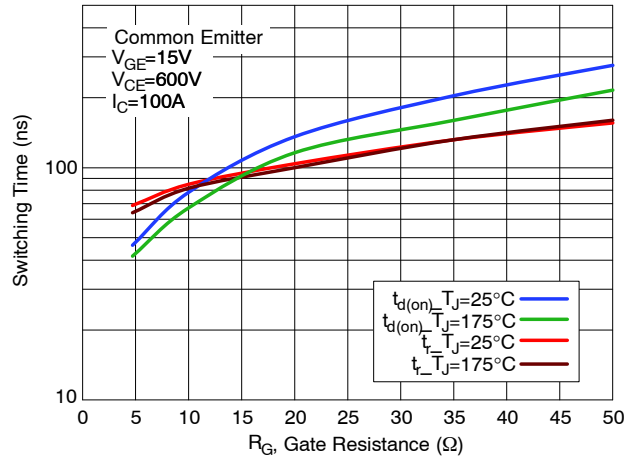


Figure 10. Turn-On Switching Time vs. Gate Resistance

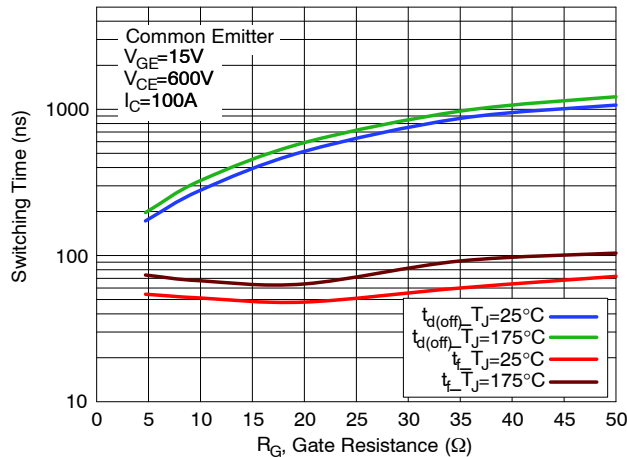


Figure 11. Turn-Off Switching Time vs. Gate Resistance

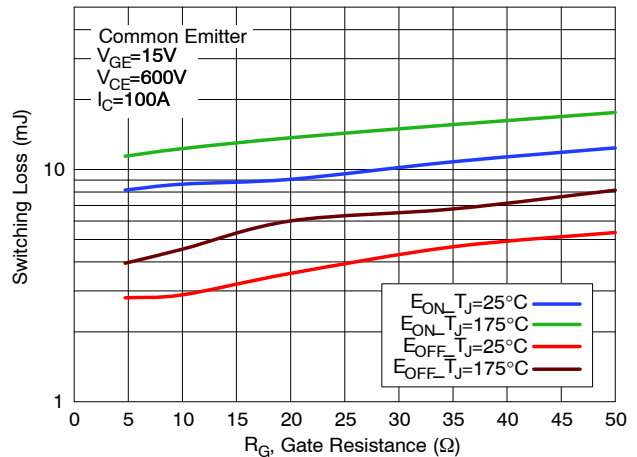


Figure 12. Switching Loss vs. Gate Resistance

FGY100T120SWD

TYPICAL CHARACTERISTICS

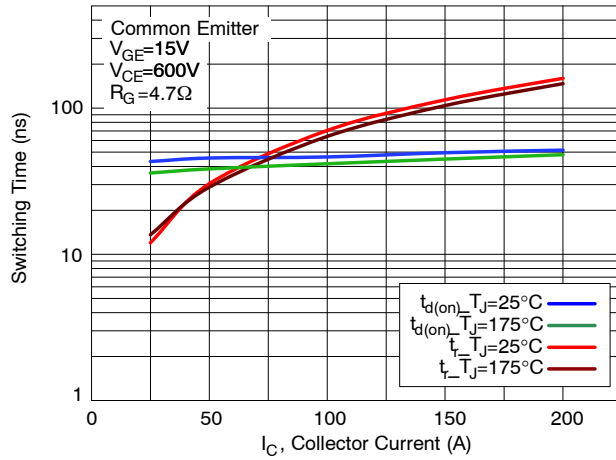


Figure 13. Turn-On Switching Time vs. Collector Current

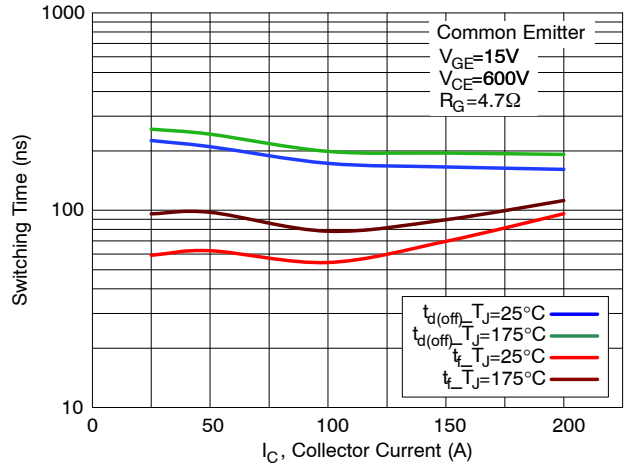


Figure 14. Turn-Off Switching Time vs. Collector Current

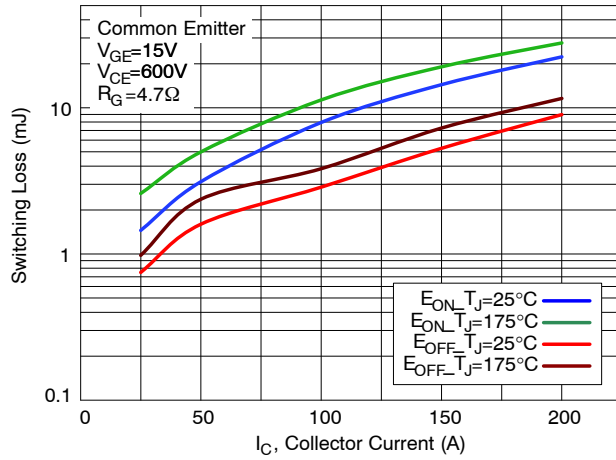


Figure 15. Switching Loss vs. Collector Current

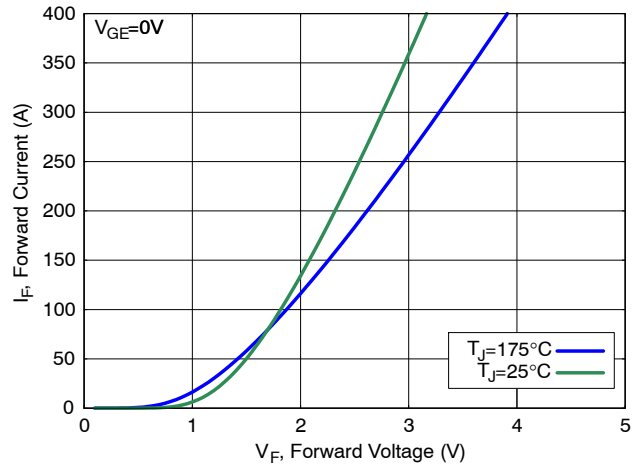


Figure 16. Diode Forward Characteristics

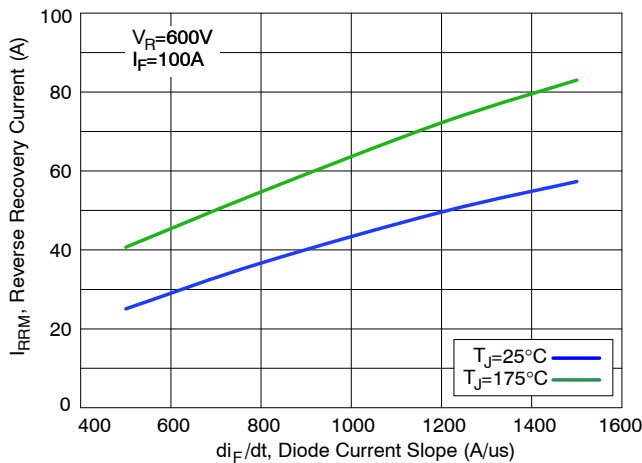


Figure 17. Diode Reverse Recovery Current

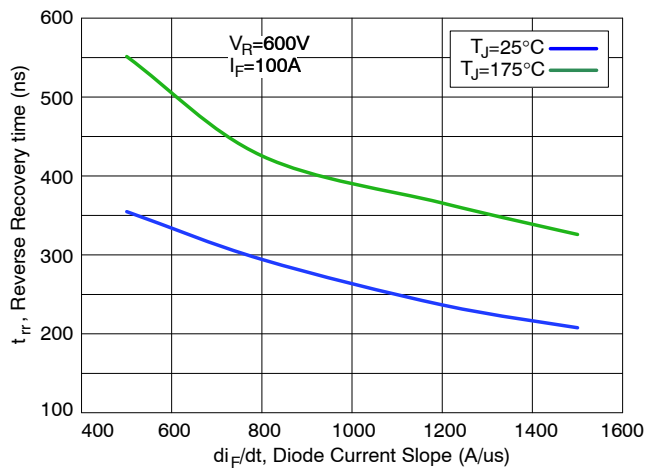


Figure 18. Diode Reverse Recovery Time

FGY100T120SWD

TYPICAL CHARACTERISTICS

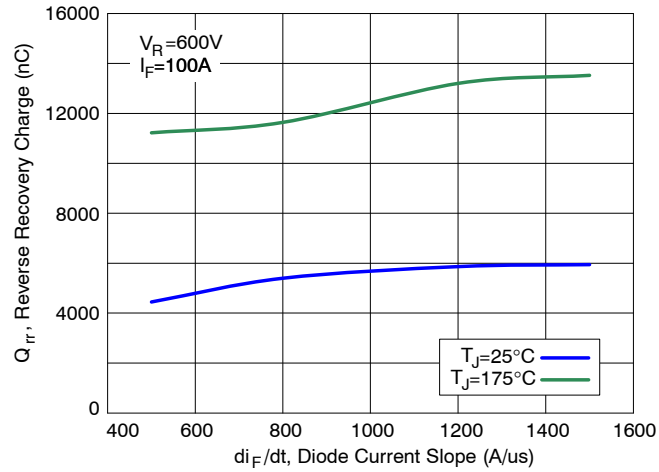


Figure 19. Diode Stored Charge Characteristics

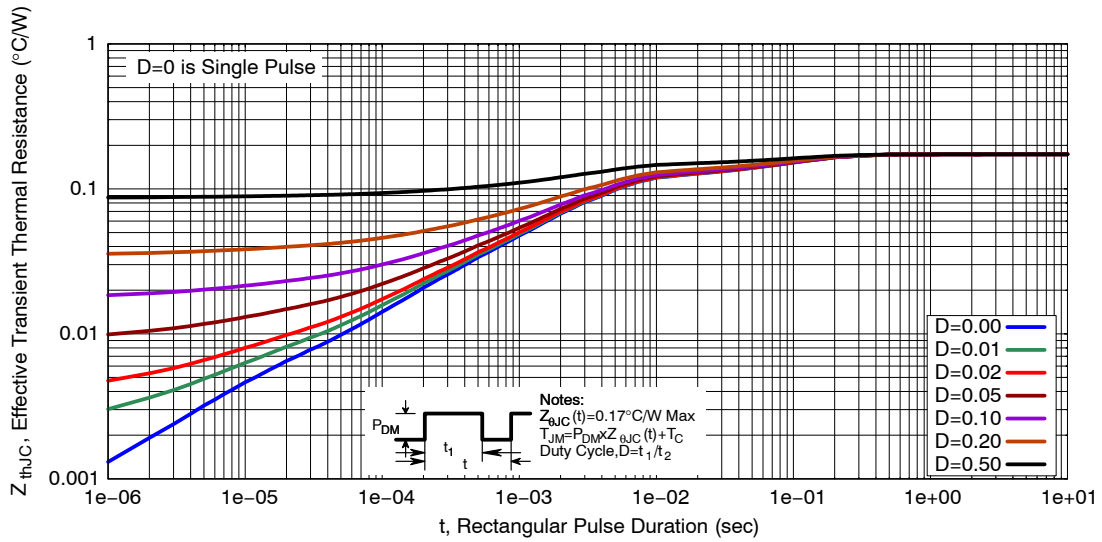


Figure 20. Transient Thermal Impedance of IGBT

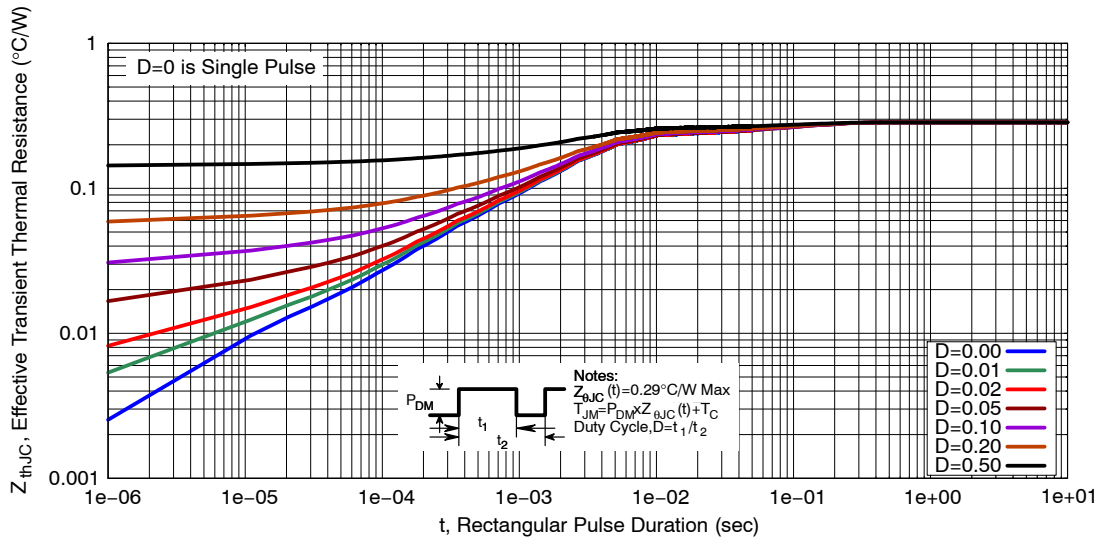
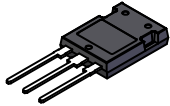


Figure 21. Transient Thermal Impedance of Diode

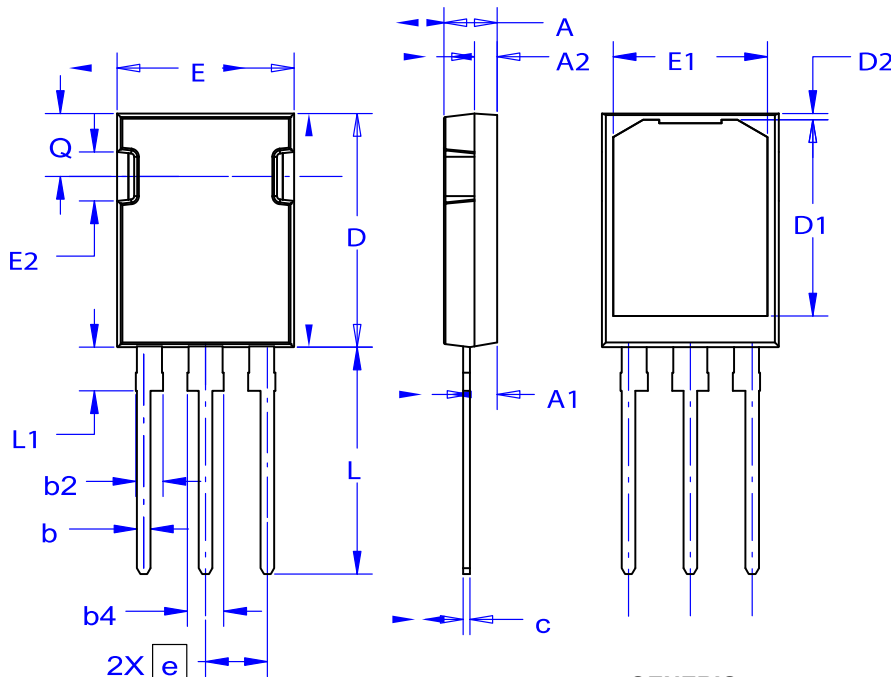


TO-247-3LD
CASE 340CD
ISSUE A

DATE 18 SEP 2018

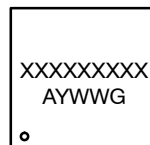
NOTES:

- A. THIS PACKAGE DOES NOT CONFORM TO ANY STANDARDS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.12	4.32	4.52
e	~	5.45	~
L	19.90	20.00	20.10
L1	3.69	3.81	3.93
Q	5.34	5.46	5.58
b	1.10	1.20	1.30
b2	2.10	2.24	2.39
b4	2.87	3.04	3.20
c	0.51	0.61	0.71
D1	16.63	16.83	17.03
D2	0.51	0.93	1.35
E1	13.40	13.60	13.80

**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON13857G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-247-3LD	PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales